Vishay Semiconductors

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Hyperfast Rectifier, 2 x 5 A FRED Pt[®]



PRIMARY CHARACTERISTICS									
I _{F(AV)}	2 x 5 A								
V _R	200 V								
V _F at I _F	0.74 V								
t _{rr} (typ.)	23 ns								
T _J max.	175 °C								
Package	DPAK (TO-252AA)								
Circuit configuration	Common cathode								

FEATURES

- Hyperfast recovery time
- 175 °C max. operating junction temperature
- Output rectification freewheeling
- Low forward voltage drop reduced Q_{rr} and soft recovery
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS											
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS							
Peak repetitive reverse voltage	V _{RRM}		200	V							
Average rectified forward current	I _{F(AV)}	T _C = 160 °C	10	Δ							
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	A							
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C							

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-					
Forward voltage		I _F = 5 A	-	0.90	0.98					
	V _F	I _F = 10 A	0.98	1.15	V					
		I _F = 5 A, T _J = 150 °C	-	0.74	0.84					
		I _F = 10 A, T _J = 150 °C	-	0.84	1.05					
		$V_{\rm R} = V_{\rm R}$ rated	-	-	4					
Reverse leakage current per leg	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	40	μA				
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	80					
Junction capacitance per leg	C _T	V _R = 600 V	-	17	-	pF				
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8	-	nH				

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RoHS COMPLIANT HALOGEN

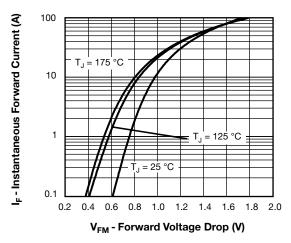


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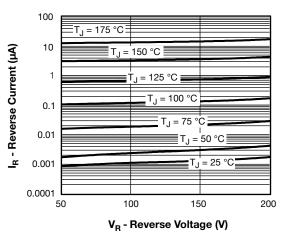
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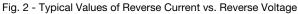
DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \degree C$ unless otherwise specified)											
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS				
		I _F = 1 A, dI _F /dt =	= 100 A/µs, V _R = 30 V	-	23	27					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	21	-	ns				
		T _J = 125 °C		-	26	-					
Peak recovery current	I _{RRM}	T _J = 25 °C	$I_{\rm F} = 5 {\rm A}$	-	2	-	A				
Feat recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	3.1	-					
Poverse recovery charge	Q _{rr}	T _J = 25 °C		-	20	-	nC				
Reverse recovery charge	Qrr	T _J = 125 °C		-	41	-	nC				

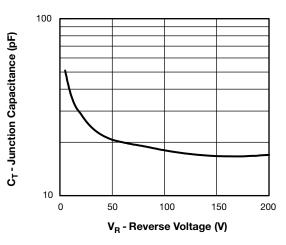
THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage tempe	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case	per leg	R _{thJC}		-	2.7	3.2	°C/W			
	per device			-	1.35	1.6				
Approximate weight					0.3		g			
					0.01		oz.			
Marking device			Case style DPAK (TO-252AA)	10CWH02FN						

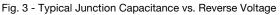












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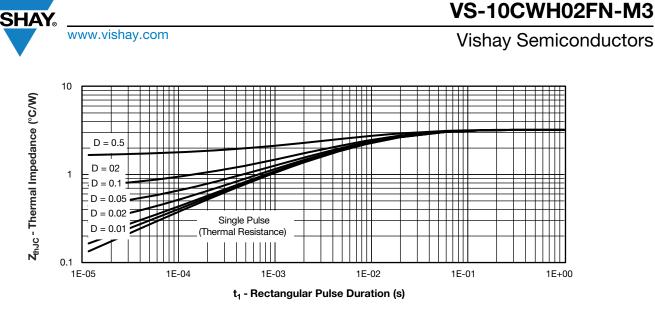


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

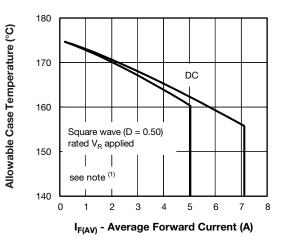
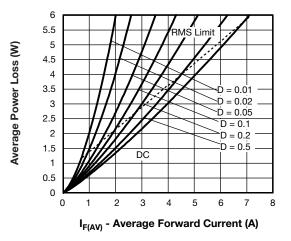


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

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40 35 30 5 Å, T_J = 25 125 t_{rr} (nC) 20 15 5 A, T_{.1} = 25 °C 10 5 0 100 1000 dl_Fdt (A/µs)

Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

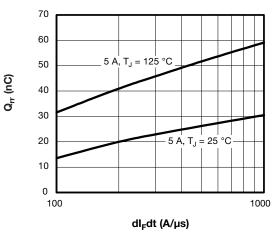


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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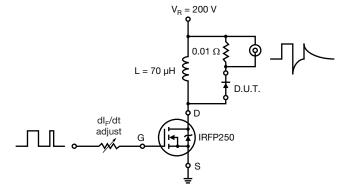


Fig. 9 - Reverse Recovery Parameter Test Circuit

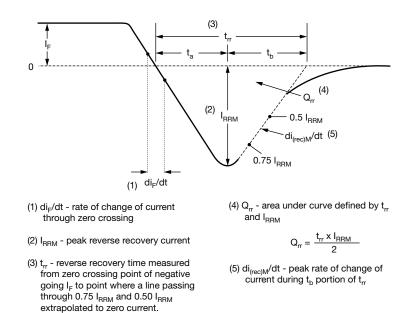


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

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SHA

Device code	VS-	10	с	w	н	02	FN	TRL	-МЗ
	(1)	(2)	(3)	(4)	(5)	6	(7)	(8)	(9)
	1	- Visl	nay Sen	nicondu	ctors pro	oduct			
	2	- Cur	rent rati	ng (10 =	= 10 A)				
	3	- Circ	cuit conf	iguratio	า:				
		C =	commo	on catho	de				
	4	- Pac	kage id	entifier:					
	_	VV =	D-PAK	(
	Ľ			ast recov	-				
	Ľ		-	ing (02 =	= 200 V)				
	7		= TO-25						
	8		one = tu						
			-	e and re					
				be and r					
	_		-	pe and r		nt orient	ed)		
	9	- Env	rironmer	ntal digit	:				
		-M3	s = halog	gen-free	, RoHS-	-complia	ant and	termina	tions le

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-10CWH02FN-M3	75	3000	Antistatic plastic tube						
VS-10CWH02FNTR-M3	2000	2000	13" diameter reel						
VS-10CWH02FNTRL-M3	3000	3000	13" diameter reel						
VS-10CWH02FNTRR-M3	3000	3000	13" diameter reel						

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95627							
Part marking information	www.vishay.com/doc?95176							
Packaging information	www.vishay.com/doc?95033							
SPICE model	www.vishay.com/doc?95376							

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D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	2.18	2.39	0.086	0.094		е	2.29	BSC	0.090	BSC	
A1	-	0.13	-	0.005		Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035		L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045		L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3	L2	0.51	BSC	0.020	BSC	
с	0.46	0.61	0.018	0.024		L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035		L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5	L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3	Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5	Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3	Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC[®] outline TO-252AA



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